

BSS84/BSS110

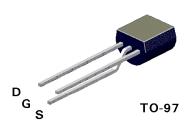
P-Channel Enhancement Mode Field Effect Transistor

General Description

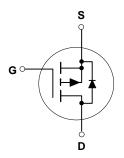
These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. They can be used, with a minimum of effort, in most applications requiring up to 0.17A DC and can deliver pulsed currents up to 0.68A. This product is particularly suited to low voltage applications requiring a low current high side switch.

Features

- \blacksquare BSS84: -0.13A, -50V. $R_{\rm DS(ON)}$ = 10 Ω @ $\rm V_{\rm GS}$ = -5V. BSS110: -0.17A, -50V. $R_{\rm DS(ON)} = 10\Omega$ @ $V_{\rm GS} = -10V$
- Voltage controlled p-channel small signal switch.
- High density cell design for low R_{DS(ON)}.
- High saturation current.







Absolute Maximum Patings

T = 25°C unlose othorwise noted

Symbol	Parameter	BSS84	BSS110	Units			
V _{DSS}	Drain-Source Voltage	-	-50				
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 20 \text{ K}\Omega$)	-	50	V			
V_{GSS}	Gate-Source Voltage - Continuous	±	±20				
I _D	Drain Current - Continuous @ T _A = 30/35°C	-0.13	-0.17	А			
	- Pulsed @ $T_A = 25^{\circ}C$	-0.52	-0.68				
P_{D}	Maximum Power Dissipation T _A = 25°C	0.36	0.63	W			
T _J ,T _{STG}	Operating and Storage Temperature Range	-55	°C				
T _L	Maximum lead temperature for soldering purposes, 1/16" from case for 10 seconds	3	°C				
THERMA	L CHARACTERISTICS			•			
R _{0JA}	Thermal Resistance, Junction-to-Ambient	350	°C/W				

Symbol	Parameter	Conditions	1	Гуре	Min	Тур	Max	Units
OFF CHA	RACTERISTICS							
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		All	-50			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -50 \text{ V},$		All			-15	μΑ
		$V_{GS} = 0 \text{ V}$ $T_J = 125^{\circ}$					-60	μΑ
		$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$					-0.1	μΑ
I _{GSSR}	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$		All			-10	nA
ON CHA	RACTERISTICS (Note 1)							
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -1 \text{ mA}$		All	-0.8	-1.75	-2	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -5V, I_{D} = -0.10 A$	В	SS84		3.2	10	Ω
		$V_{GS} = -10 \text{ V}, I_{D} = -0.17 \text{ A}$	BS	SS110		2.2	10	
g _{FS}	Forward Transconductance	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{A}$	В	SS84	0.05	0.27		S
		$V_{DS} = -10 \text{ V}, I_{D} = -0.17 \text{ A}$	BS	SS110	0.05	0.29		
DYNAMIC	CHARACTERISTICS							
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, \ V_{GS} = 0 \text{ V}, $ f = 1.0 MHz	В	SS84		37	45	pF
		t = 1.0 MHz	BS	SS110		37	40	
C _{oss}	Output Capacitance			All		16	25	pF
C _{rss}	Reverse Transfer Capacitance			All		5	12	pF
	NG CHARACTERISTICS (Note 1)							
t _{D(on)}	Turn - On Delay Time	$V_{DD} = -30 \text{ V}, I_{D} = -0.27 \text{ A},$		All			12	nS
ţ,	Turn - On Rise Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 50 \Omega$		All			50	nS
t _{D(off)}	Turn - Off Delay Time			All			10	nS
ţ,	Turn - Off Fall Time	fum - Off Fall Time					25	nS
	DURCE DIODE CHARACTERISTICS							
I _s	Continuous Source Diode Current		В	SS84			-0.13	Α
5			BS	SS110			-0.17	
I _{SM}	Maximum Pulsed Source Diode Current	(Note 1)	В	SS84			-0.52	Α
Civi			BS	SS110			-0.68	
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -0.26 A (Note 1)	В	SS84		-0.95	-1.2	V
SD		$V_{GS} = 0 \text{ V}, I_S = -0.34 \text{ A (Note 1)}$	BS	SS110		-1	-1.2	

Note: 1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Typical Electrical Characteristics

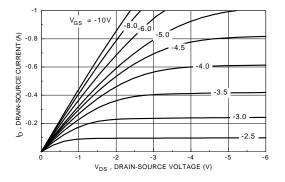


Figure 1. On-Region Characteristics

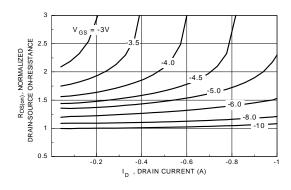


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

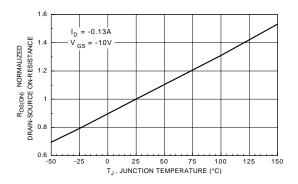


Figure 3. On-Resistance Variation with Temperature

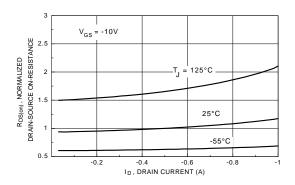


Figure 4. On-Resistance Variation with Drain Current and Temperature

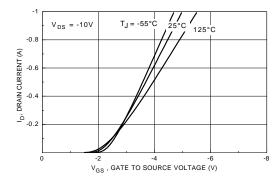


Figure 5. Transfer Characteristics

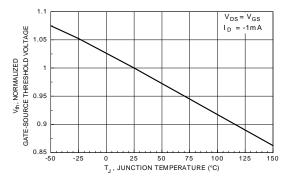


Figure 6. Gate Threshold Variation with Temperature

Typical Electrical Characteristics (continued)

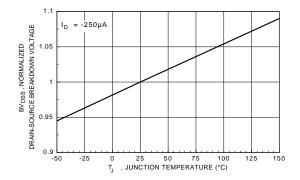


Figure 7. Breakdown Voltage Variation with Temperature

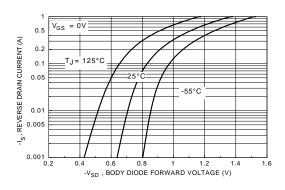


Figure 8. Body Diode Forward Voltage Variation with Source Current and Temperature

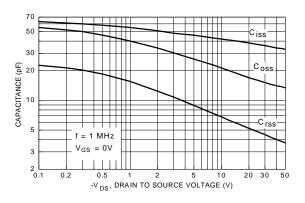


Figure 9. Capacitance Characteristics

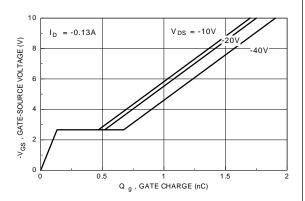


Figure 10. Gate Charge Characteristics

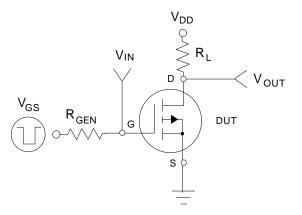


Figure 11. Switching Test Circuit

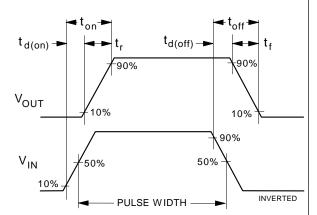
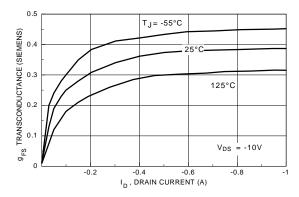


Figure 12. Switching Waveforms

Typical Electrical Characteristics (continued)



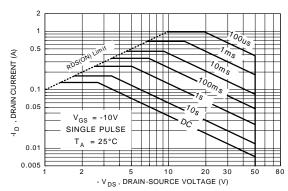


Figure 13. Transconductance Variation with Drain Current and Temperature

Figure 14. Maximum Safe Operating Area

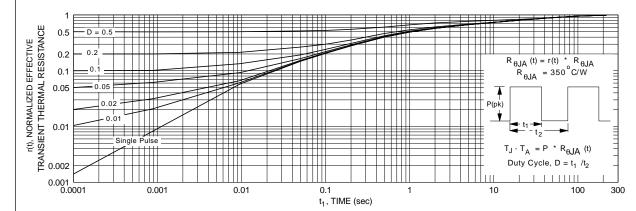


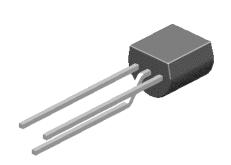
Figure 15. Transient Thermal Response Curve

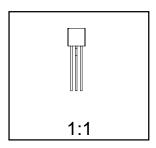
Note: Characterization performed using a circuit board with 175°C/W typical case-to-ambient thermal resistance.

TO-92 Package Dimensions



TO-92; TO-18 Reverse Lead Form (J35Z Option) (FS PKG Code 92, 94, 96)

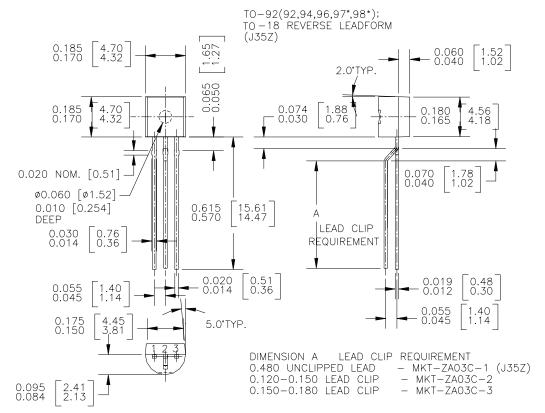




Scale 1:1 on letter size paper

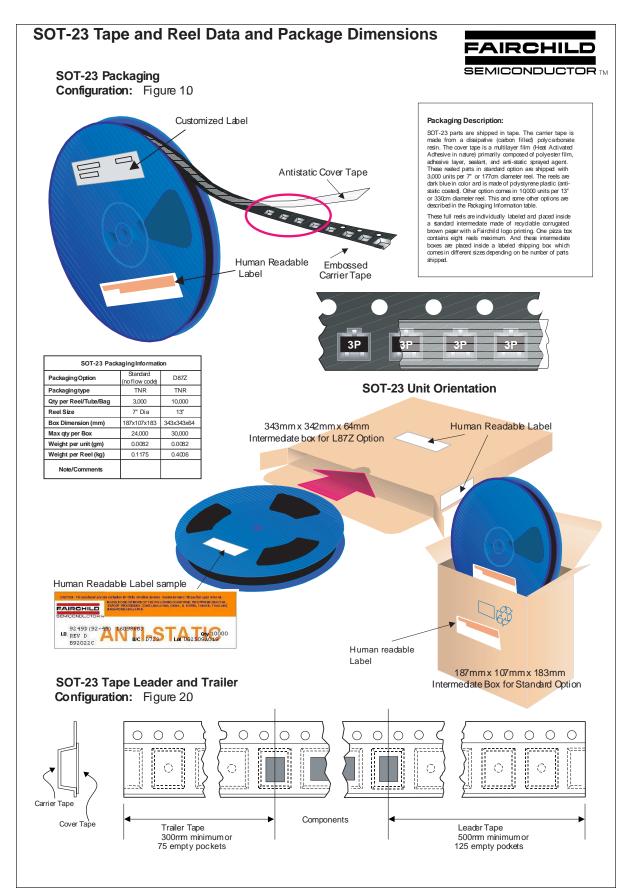
Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.22



Note: All package 97 or 98 transistors are leadformed to this configuration prior to bulk shipment. Order L34Z option if in-line leads are preferred on package 97 or 98.

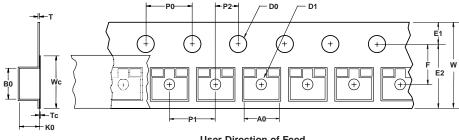
^{*} Standard Option on 97 & 98 package code



SOT-23 Tape and Reel Data and Package Dimensions, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



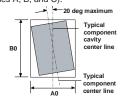
User Direction of Feed	

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



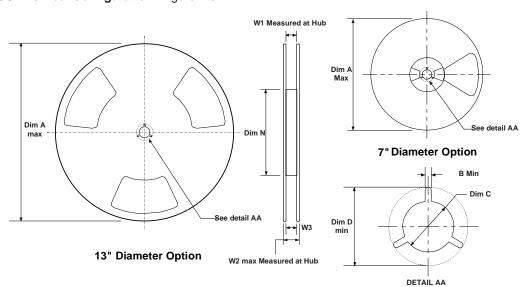
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

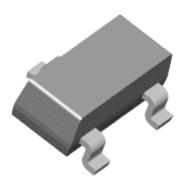
SOT-23 Reel Configuration: Figure 4.0

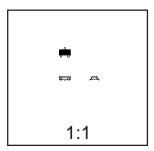


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Tape and Reel Data and Package Dimensions, continued

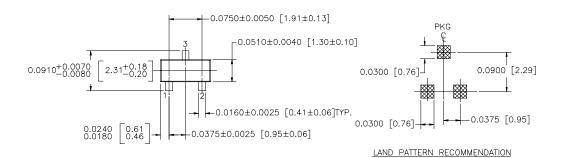
SOT-23 (FS PKG Code 49)

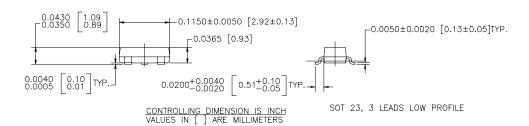




Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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